

# WAT-226 High Power Wafer Test System

## Description

Power device testing needs to be carried out under extreme test conditions such as high temperature of 350°C, low temperature of -70°C, high voltage of 10KV, high current of 600A, etc. In order to protect the device from being affected by various extreme conditions during the test (such as oxidation, junction Dew, frost, arc breakdown and other physical damage and pollution), ETSC Group has launched the High-Power Wafer Test System (WAT-226) which is suitable for SiC/GaN third-generation semiconductors.

WAT-226 adopts the form of a closed chamber. Moving components, heating components, cooling components, wafer chucks, probe stations, probe arms and other components used for testing are all concentrated in a sealed cavity to build a safe wafer-level test environment for power devices, which meets high-low temperature, high pressure, high flow and other extreme conditions of testing requirements.



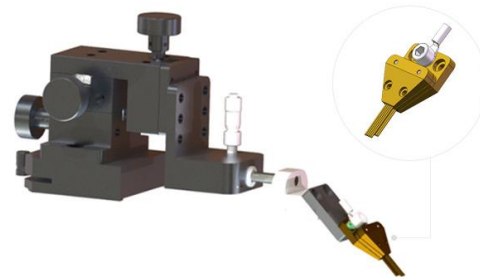
## Features

- Suitable for SiC/GaN third-generation semiconductors
- High vacuum and low deformation cavity design
- High Voltage : > 10 kV @ 1mm
- High current : > 600A
- Temperature control range: -55°C to 300°C (wider range can be customized)
- Vacuum: <1e-4 Torr
- Optional high voltage and high current probes

## Self-developed core components

### High current probe

- Probe Tip: Curved and Flexible Design
- Single row 600A
- Double row 1200A
- Probe holder with parallel adjustment



### High voltage probe

- Tungsten needle tip
- Ceramic Needle Arm
- High voltage > 20kV

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